TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74LVX573F,TC74LVX573FT

Octal D-Type Latch with 3-State Output

The TC74LVX573F/ FT is a high-speed CMOS octal latch with 3-state output fabricated with silicon gate CMOS technology. Designed for use in 3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

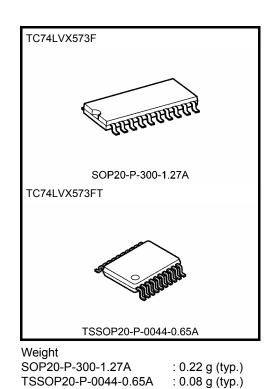
This device is suitable for low-voltage and battery operated systems.

This 8 bit D-type latch is controlled by a latch enable input (LE) and an output enable input (\overline{OE}). When the \overline{OE} input is high, the eight outputs are in a high-impedance state.

An input protection circuit ensures that 0 to 5.5V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

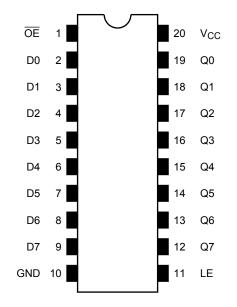
Features

- High speed: $t_{pd} = 6.4 \text{ ns} (typ.) (V_{CC} = 3.3 \text{ V})$
- Low-power dissipation: $I_{CC} = 4 \mu A (max) (Ta = 25^{\circ}C)$
 - Input voltage level: $V_{IL} = 0.8 V (max) (V_{CC} = 3 V)$
 - $V_{IH} = 2.0 V (min) (V_{CC} = 3 V)$
- Power-down protection provided on all inputs
- Balanced propagation delays: $t_{pLH}\simeq t_{pHL}$
- Low noise: $V_{OLP} = 0.8 V (max)$
- Pin and function compatible with 74HC573

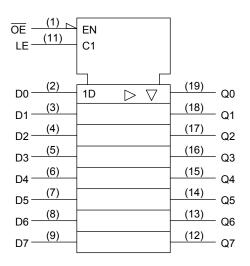


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Pin Assignment (top view)



IEC Logic Symbol



Truth Table

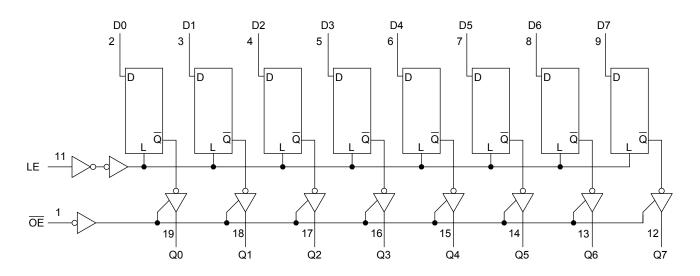
	Outputs		
ŌĒ	LE	Outputs	
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5 to 7.0	V
DC input voltage	V _{IN}	-0.5 to 7.0	V
DC output voltage	V _{OUT}	-0.5 to V_{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	IOK	±20	mA
DC output current	IOUT	±25	mA
DC V _{CC} /ground current	ICC	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0 to 3.6	V
Input voltage	V _{IN}	0 to 5.5	V
Output voltage	V _{OUT}	0 to V _{CC}	V
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 100	ns/V

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics Sym- bol Test Con					Ta = 25°C		Ta = -40 to 85°C		Unit		
			$V_{CC}(V)$	Min	Тур.	Max	Min	Max			
					2.0	1.5	_	_	1.5	_	
	H-level	VIH		_		2.0	—	_	2.0	—	
Input voltage					3.6	2.4	—	_	2.4	—	v
input voltage					2.0	_	—	0.5	_	0.5	v
	L-level	VIL		_	3.0	_	—	0.8	_	0.8	
						_	—	0.8	_	0.8	
	H-level \		V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	2.0	1.9	2.0	_	1.9	—	v
		V _{OH}		I _{OH} = -50 μA	3.0	2.9	3.0	_	2.9	—	
Output voltage				I _{OH} = -4 mA	3.0	2.58	—	_	2.48	—	
Output voltage		level V _{OL}		$I_{OL} = 50 \ \mu A$	2.0	_	0	0.1	_	0.1	v
	L-level		V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	3.0	_	0	0.1	_	0.1	1
				$I_{OL} = 4 \text{ mA}$	3.0	_	—	0.36	_	0.44	
3-state output $V_{IN} = V_{IH}$ or V_{IL}		3.6			±0.25		±2.5				
Off-state current I_{OZ} $V_{OUT} = V_{CC}$ or GN		CC or GND	5.0			10.25		12.5	μA		
Input leakage curre	t leakage current I _{IN} V _{IN} = 5.5 V or GND		/ or GND	3.6	_	—	±0.1	_	±1.0	μA	
Quiescent supply current I_{CC} $V_{IN} = V_{CC}$ or GND		3.6		_	4.0		40.0	μA			

Timing Requirements (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	DI Test Condition		Ta = 25°C	Ta =40 to 85°C	Unit
		$V_{CC}(V)$	Limit	Limit		
Minimum pulse width	t		2.7	6.5	7.5	ns
(LE)	t _{W (H)}	_	$\textbf{3.3}\pm\textbf{0.3}$	5.0	5.0	115
Minimum set-up time	ts		2.7	5.0	5.0	ns
		_	$\textbf{3.3}\pm\textbf{0.3}$	3.5	3.5	115
Minimum hold time	t _h		2.7	1.5	1.5	ns
		_	$\textbf{3.3}\pm\textbf{0.3}$	1.5	1.5	115

AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -40 to 85°C		Unit
			V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	
	+		2.7	15		8.2	15.6	1.0	18.5	ns
Propagation delay time	^t pLH		2.1	50	_	10.7	19.1	1.0	22.0	
(LE-Q)	+		3.3 ± 0.3	15	_	6.4	10.1	1.0	12.0	115
	t _{pHL}		3.3 ± 0.3	50	_	8.9	13.6	1.0	15.5	
	+		2.7	15	_	7.6	14.5	1.0	17.5	
Propagation delay time	t _{pLH}		2.7	50	_	10.1	18.0	1.0	21.0	ns
(D-Q)	t _{pHL}			15	_	5.9	9.3	1.0	11.0	
			$\textbf{3.3}\pm\textbf{0.3}$	50	_	8.4	12.8	1.0	14.5	
	t _{pZL}	R _L = 1 kΩ	2.7	15	_	7.8	15.0	1.0	18.5	- ns
Output anabla time				50	_	10.3	18.5	1.0	22.0	
Output enable time	t _{pZH}		3.3 ± 0.3	15	_	6.1	9.7	1.0	12.0	
			3.3 ± 0.3	50	_	8.6	13.2	1.0	15.5	
Output dischla time	t _{pLZ}	5 (1.5	2.7	50		12.1	19.1	1.0	22.0	20
Output disable time	t _{pHZ}	$R_L = 1 \ k\Omega$	$\textbf{3.3}\pm\textbf{0.3}$	50	_	10.1	13.6	1.0	15.5	ns
	t _{osLH}	(Note 1)	2.7	50			1.5		1.5	
Output to output skew	t _{osHL}	(NOLE T)	$\textbf{3.3}\pm\textbf{0.3}$	50			1.5		1.5	ns
Input capacitance	CIN			(Note 2)		4	10		10	pF
Output capacitance	COUT		_		_	6	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note 3)	_	29	_	_	_	pF

- Note 1: Parameter guaranteed by design. $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$
- Note 2: Parameter guaranteed by design.
- Note 3: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per latch)

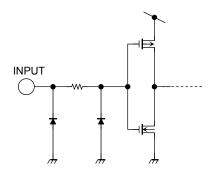
And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation: C_{PD} (total) = $21 + 8 \cdot n$

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Noise Characteristics (Ta = 25°C, input: $t_r = t_f = 3 \text{ ns}, C_L = 50 \text{ pF}$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Limit	Unit
Quiet output maximum dynamic V_{OL}	V _{OLP}	—	3.3	0.5	0.8	V
Quiet output minimum dynamic V_{OL}	V _{OLV}	—	3.3	-0.5	-0.8	V
Minimum high level dynamic input voltage V_{IH}	V _{IHD}	—	3.3	_	2.0	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	_	3.3	_	0.8	V

Input Equivalent Circuit

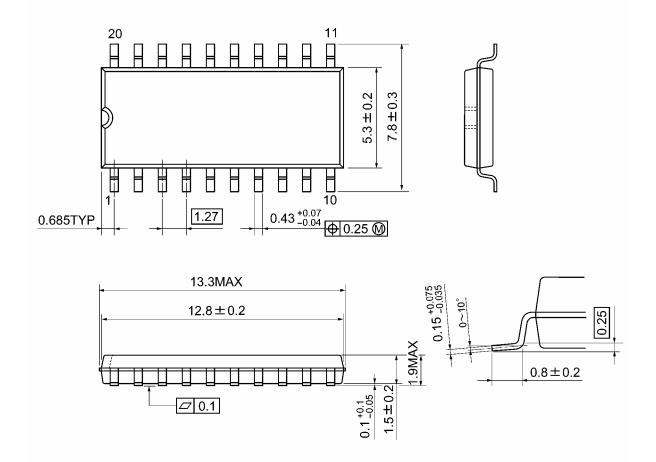


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Package Dimensions

SOP20-P-300-1.27A

Unit: mm



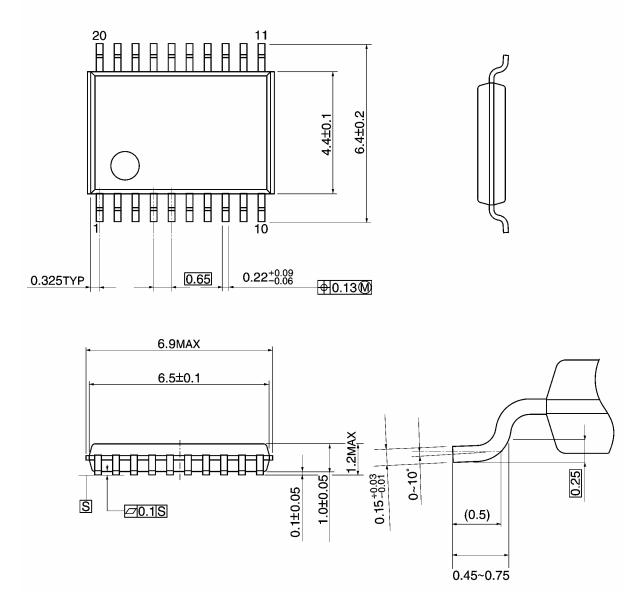
Weight: 0.22 g (typ.)

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Package Dimensions

TSSOP20-P-0044-0.65A

Unit: mm



Weight: 0.08 g (typ.)

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20070701-EN GENERAL

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